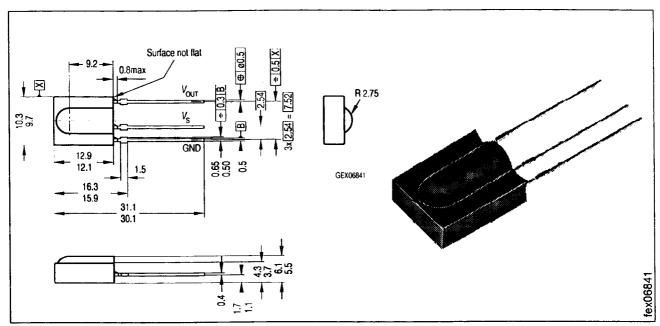


IR-Empfänger/Demodulator-Baustein IR-Receiver/Demodulator Device



Maße in mm, wenn nicht anders angegeben/Dimensions in mm, unless otherwise specified.

Wesentliche Merkmale

- Fotodiode mit integriertem Verstärker
- Angepaßt an verschiedene Trägerfrequenzen
- Gehäuse schwarz eingefärbt: Verguß optimiert für eine Wellenlänge von 950 nm
- Hohe Störsicherheit
- Geringe Stromaufnahme
- 5 V Betriebsspannung
- Hohe Empfindlichkeit
- TTL und CMOS kompatibel
- Verwendbar bis zu einem Tastverhältnis ≤ 40 %

Anwendungen

• Empfänger für IR-Fernsteuerungen

Features

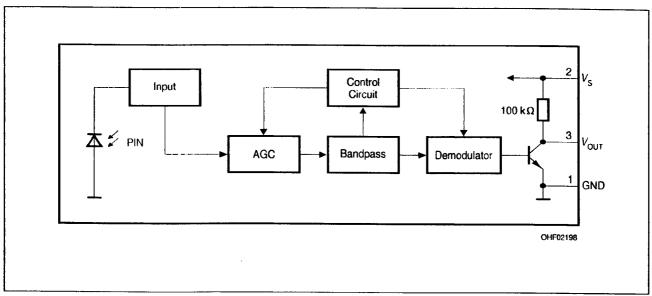
- Photodiode with hybride integrated circuit
- Available for several carrier frequencies
- Black epoxy resin, daylight filter optimized for 950 nm
- High immunity against ambient light
- Low power consumption
- 5 V supply voltage
- High sensitivity (internal shield case)
- TTL and CMOS compatibility
- Continuous transmission possible $(t_p/T \le 0.4)$

Applications

• IR-remote control preamplifier modules

Тур	Trägerfrequ.	Bestellnr.	Тур	Trägerfrequ.	Bestellnr.
Туре	Carrier Frequency kHz	Ordering Code	Туре	Carrier Frequency kHz	Ordering Code
SFH 506-30	30	Q62702-P1196	SFH 506-38	38	Q62702-P1199
SFH 506-33	33	Q62702-P1197	SFH 506-40	40	Q62702-P1200
SFH 506-36	36	Q62702-P1198	SFH 506-56	56	Q62702-P1201





Blockschaltbild Block Diagram

Grenzwerte Maximum Ratings

Bezeichnung Description		Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operation and storage temperature	range	T_{A},T_{stg}	- 25 + 85	°C
Sperrschichttemperatur Junction temperature range		$T_{\mathbf{i}}$	100	°C
Löttemperatur Lötstelle 2 mm vom Gehäuse; Lötze Soldering temperature soldering joint ≥ 2 mm distance from package, soldering time $t \leq 5$ s		T _S	260	°C
Betriebsspannung Supply voltage	Pin 2	V _s	- 0.3 + 6.0	V
Betriebsstrom Supply current	Pin 2	I _{cc}	5	mA
Ausgangsspannung Output voltage	Pin 3	V _{OUT}	- 0.3 + 6.0	V
Ausgangsstrom Output current	Pin 3	I _{OUT}	5	mA
Verlustleistung Total power dissipation $T_A \le 85 ^{\circ}\text{C}$		P _{tot}	50	mW

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Kennwerte ($T_A = 25$ °C) Characteristics

Bezeichnung Description	Symbol Symbol	Wert Value	Einheit Unit
Betriebsspannung Supply voltage	$V_{\mathtt{S}}$	typ. 5.0 (4.5 5.5)	V
Bestrahlungsstärke (Testsignal, s. Figure 2) Threshold irradiance (test signal, see Fig. 2)	$E_{\rm e min(30-40 kHz)}^{(30-40 kHz)}$ $E_{\rm e min(56 kHZ)}^{(1)}$ $E_{\rm e max}^{(1)}$	typ. 0.35 (< 0.5) typ. 0.4 (< 0.6) 30	mW/m ² W/m ²
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	λ _{s max}	950	nm
Spektraler Bereich der Fotoempfindlichkeit Range of spectral sensitivity $S = 10 \%$ of S_{max}	Δλ	830 1100	nm
Halbwinkel Half angle	φ	± 45	deg.
Stromaufnahme Pin 2 Current consumption $V_s = 5 \text{ V}, E_v = 0$ $V_s = 5 \text{ V}, E_v = 40 000 \text{ lx}, \text{ sunlight}$	I _{CC}	0.6 (< 0.8) 1.0	mA mA
Ausgangsspannung Pin 3 Output voltage $I_{\rm OUT}=0.5~{\rm mA}, E_{\rm e}=0.7~{\rm mW/m^2}, f=f_0, T_{\rm p}/T=0.4$	V _{OUT low}	< 250	mV

¹⁾ In Verbindung mit einer typ. SFH 415 bei Betrieb mit $I_{\rm F}$ = 0.5 A wird eine Reichweite von ca. 35 m erreicht.

Together with an IRED SFH 415 under operation conditions of $I_{\rm F} = 0.5$ A a distance of 35 m is possible.



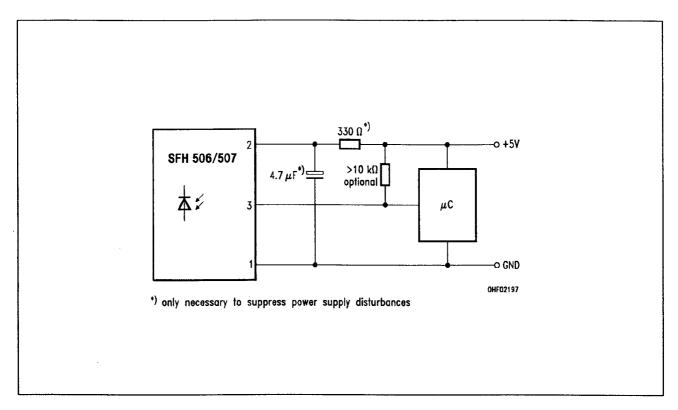


Figure 1 Externe Beschaltung External circuit

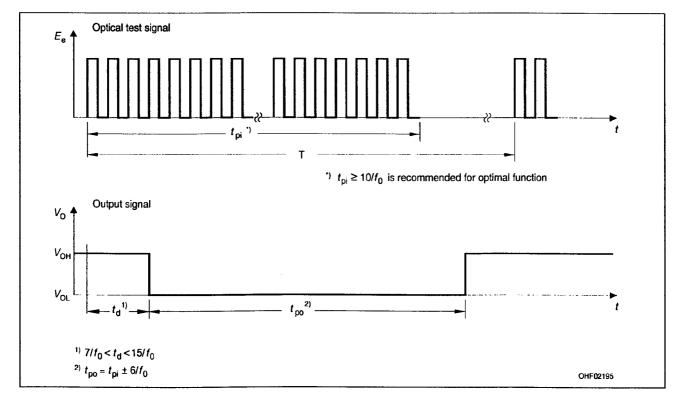
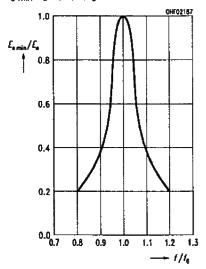


Figure 2 Testsignal Test signal

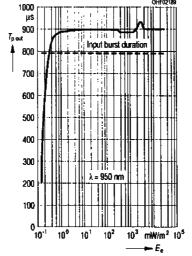
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Relative sensitivity

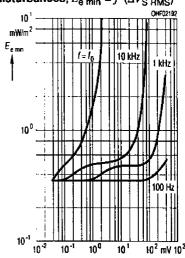
 $E_{\text{e min}}/E_{\text{e}} = f (f/f_0)$



Sensitivity vs. dark ambient $T_{p \text{ out}} = f(E_e)$ $\lambda = 950$ nm, optical test signal



Sensitivity vs. supply voltage disturbances, $E_{e \text{ min}} = f (\Delta V_{S \text{ RMS}})$



Sensitivity vs. electric field disturbance $E_{e \, min} = f \, (E)$, field strength of disturbance, $f = f_0$

2.2 mW/m²

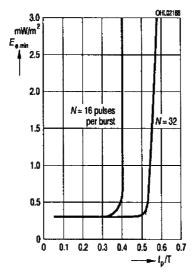
1.6

8.0

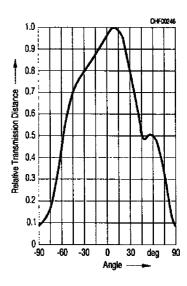
0.0 L 0.0

Sensitivity vs. duty cycle

 $E_{\mathbf{e}} = f \left(t_{p} / T \right)$

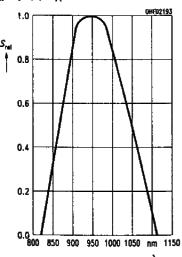


Vertical directivity φ_ν



Relative luminous intensity

 $S_{\text{rel}} = f(\lambda), T_{\text{A}} = 25 \, {}^{\text{o}}\text{C}$



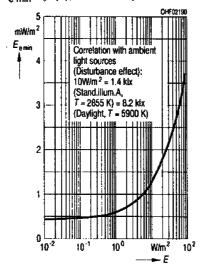
0.8

1.2 kV/m 2.0

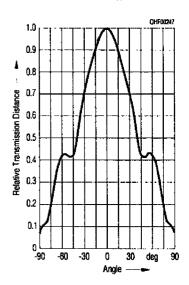
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Sensitivity vs. bright ambient

 $E_{\text{e min}} = f'(E), \lambda = 950 \text{ nm, ambient}$



Horizontal directivity ϕ_X



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Output pulse

